Abstract of Disclosure

A nitride light emitting device includes a substrate, a first nitride semiconductor stack formed above the substrate, the first nitride semiconductor stack having an epitaxial surface and a first rough surface, a distance from the epitaxial surface to the substrate being not less than a distance from the rough surface to the substrate, a nitride emitting layer formed on the epitaxial surface, and a second nitride semiconductor stack formed on the nitride emitting layer for promoting the efficiency of capturing light emitted from an LED.